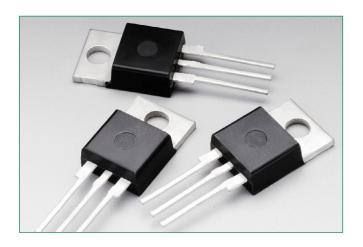
Triacs - 400V - 800V





### **Additional Information**







Accessories



**Samples** 

#### **Functional Diagram**



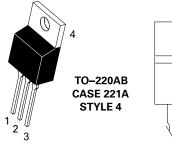
## **Description**

Designed primarily for full-wave AC control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

#### **Features**

- Blocking Voltage to 600 Volts
- All Diffused and Glass
   Passivated Junctions for
   Greater Parameter Uniformity
   and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes (Quadrants)
- Pb-Free Packages are Available







## **Maximum Ratings** $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Rating		Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (– 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V <sub>DRM</sub> , V <sub>RRM</sub>	600 800	V	
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, $T_{\rm c}$ =	: 70°C)	I <sub>T (RMS)</sub>	10	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, +25°C) Preceded and followed by rated current	I <sub>TSM</sub>	100	А	
Circuit Fusing Consideration (t = 8.3 ms)	l²t	40	A²sec	
Peak Gate Power ( $T_c = +70^{\circ}\text{C}$ , Pulse Width = 10 $\mu$ s)	$P_{GM}$	20	W	
Average Gate Power (t = 8.3 ms, $T_C = 70$ °C)	P <sub>G (AV)</sub>	0.35	W	
Peak Gate Current ( $T_c = +70$ °C, Pulse Width = 10 s)	I <sub>GM</sub>	2.0	А	
Operating Junction Temperature Range	$T_{J}$	-40 to +125	°C	
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		$T_{L}$	260	°C

## **Electrical Characteristics - OFF** ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic			Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	10	μΑ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J}^{3} = 125^{\circ}C$	I <sub>RRM</sub>	-	-	2.0	mA

### **Electrical Characteristics - ON** (T<sub>J</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (I <sub>TM</sub> = ±14 A Peak; Pulse Width =	= 1 to 2 ms, Duty Cycle ≤2%)	$V_{TM}$	-	1.2	1.65	V
	MT2(+), G(+)		-	12	50	^
Gate Trigger Current (Continuous dc)	MT2(+), G(-)	ı	_	12	50	
$(V_D = 12 V_{de}, R_1 = 100 \text{ Ohms})$	MT2(-), G(-)	GT	_	20	50	mA
D de' L	MT2(-), G(+)		-	35	75	
	MT2(+), G(+)		-	0.9	2.0	V
Gate Trigger Voltage (Continuous dc)	MT2(+), G(-)	$V_{\mathrm{GT}}$	-	0.9	2.0	
$(V_D = 12 V_{tot}, R_t = 100 \Omega)$	MT2(-), G(-)		_	1.1	2.0	
, D de, L ,	MT2(-), G(+)		-	1.4	2.5	
Holding Current ( $V_D = 12 V_{de'}$ Gate Open, Initiating Current = ±200 mA, TC=+25 °C))			_	6.0	50	mA
Turn-On Time (Rated $V_{DRM'}$ $I_{TM}$ = 14 A) ( $I_{GT}$ = 120 mA, Rise Time = 0.1 s, Pulse Width = 2 s)		t <sub>gt</sub>	-	1.5	_	μs
Gate Non–Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, RL = 100 , $T_J = +125$ °C)	All Four Quadrants	$V_{\text{GD}}$	0.2	-	-	V



not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

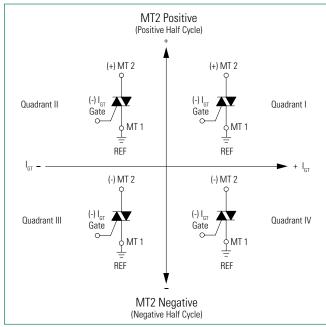
## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Commutation Voltage ( $V_D = Rated V_{DRM'} I_{TM} = 14 A$ , Commutating di/dt = 5.0 A/ms, Gate Unenergized, $T_C = 70$ °C)	di/dt(c)	-	5.0	-	V/µs
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DBM}, Exponential Waveform, Gate Open, T_C = +70°C)$	dv/dt	-	100	_	V/µs

## **Voltage Current Characteristic of SCR**

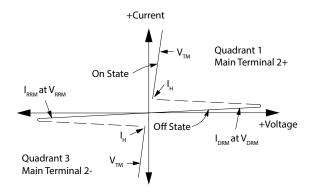
Symbol	Parameter
$V_{_{\mathrm{DRM}}}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

#### **Quadrant Definitions for a Triac**



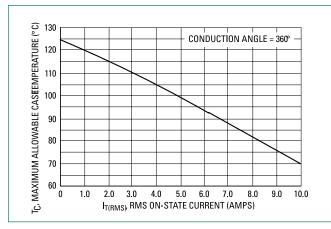
All Polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used

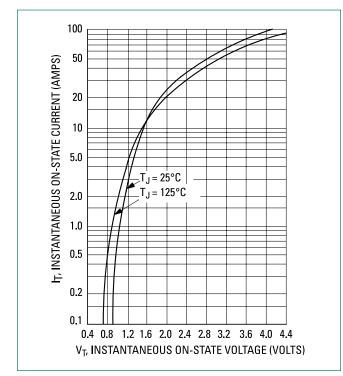


Triacs - 400V - 800V

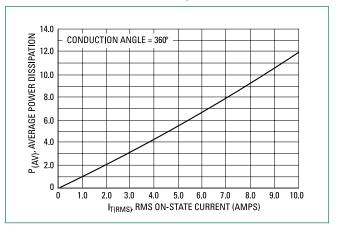
**Figure 1.**Current Derating



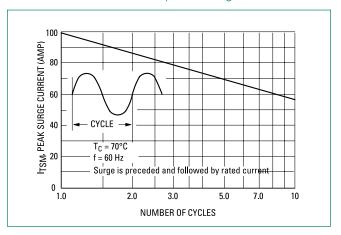
**Figure 3.** Maximum On–State Characteristics



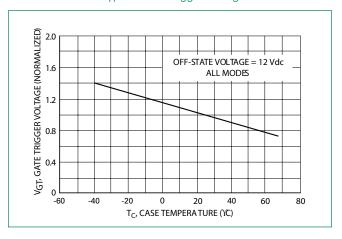
**Figure 2**. Power Dissipation



**Figure 4.**Maximum Non–Repetitive Surge Current



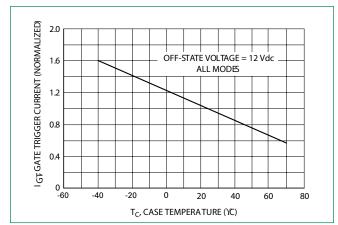
**Figure 5.**Typical Gate Trigger Voltage



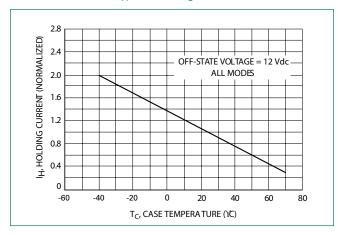


Triacs - 400V - 800V

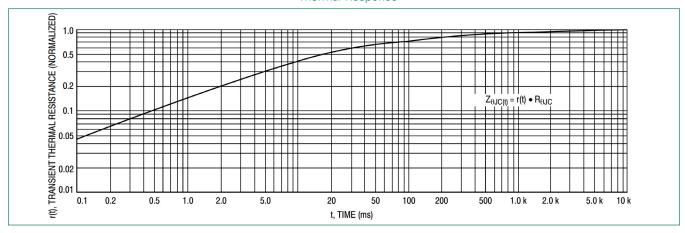
**Figure 6.**Typical Gate Trigger Current



**Figure 7.**Typical Holding Current



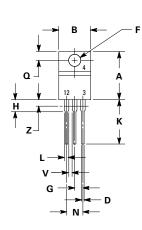
**Figure 8.**Thermal Response

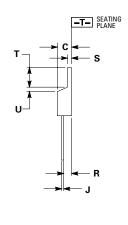




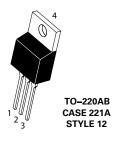
Triacs - 400V - 800V

#### **Dimensions**





#### **Part Marking System**





X	=8 or 10
Υ	=Year
M	=Month
Α	=Assembly Site
XX	=Lot Serial Code
G	=Pb-Free Packag

D:	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

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Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

## **Ordering Information**

Device	Package	Shipping
MAC210A8	TO-220AB	
MAC210A8G	TO-220AB (Pb-Free)	1000 Unite / Day
MAC210A10	TO-220AB	1000 Units/ Box
MAC210A10G	TO-220AB (Pb-Free)	

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<sup>1.</sup> Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

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MAC210A8G